

### Abstract of the Disclosure

Provided is a method of forming quantum dots in which the quantum dots are formed on a thin  $\text{In}_x\text{Ga}_{1-x}\text{As}$  strained layer. The  $\text{In}(\text{Ga})\text{As}$  quantum dots can be applied to an active layer of an optical device such as a laser diode or an optical detector.

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